

HAT1139H

Silicon P Channel Power MOS FET Power Switching

REJ03G1244-0200

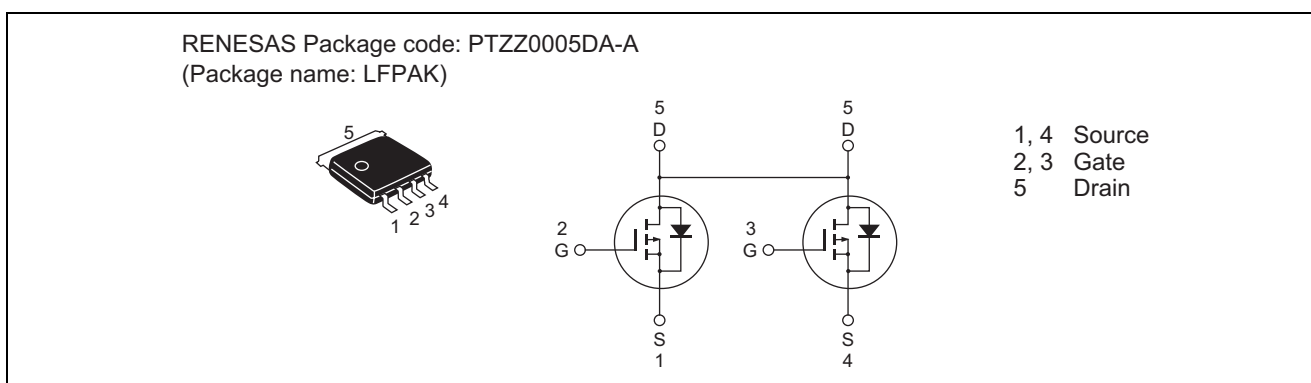
Rev.2.00

Jun.22.2005

Features

- Capable of -4.5 V gate drive
- Low drive current
- High density mounting
- Low on-resistance
 $R_{DS(on)} = 7.0\text{ m}\Omega$ typ. (at $V_{GS} = -10\text{ V}$)

Outline



Absolute Maximum Ratings

($T_a = 25^\circ\text{C}$)

Item	Symbol	Ratings	Unit
Drain to source voltage	V_{DSS}	-30	V
Gate to source voltage	V_{GSS}	-25 / +20	V
Drain current	I_D	-30	A
Drain peak current	$I_{D(pulse)}$ ^{Note1}	-120	A
Body-drain diode reverse drain current	I_{DR}	-30	A
Channel dissipation	P_{ch} ^{Note2}	15	W
Channel dissipation	P_{ch} ^{Note3}	30	W
Channel temperature	T_{ch}	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

Notes: 1. $PW \leq 10\ \mu\text{s}$, duty cycle $\leq 1\%$

2. 1 Drive operation : $T_c = 25^\circ\text{C}$

3. 2 Drive operation : $T_c = 25^\circ\text{C}$

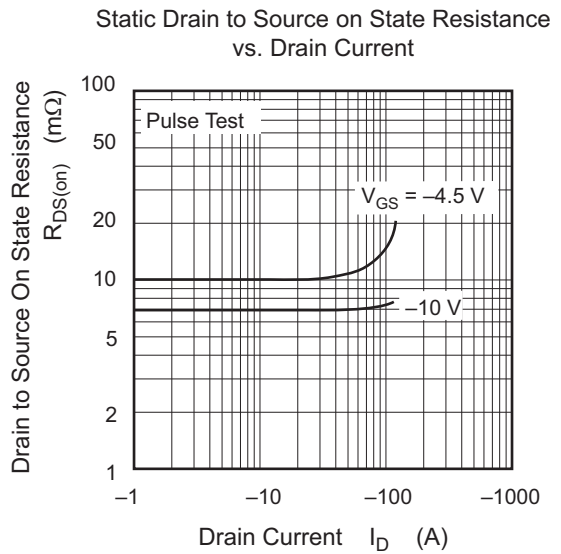
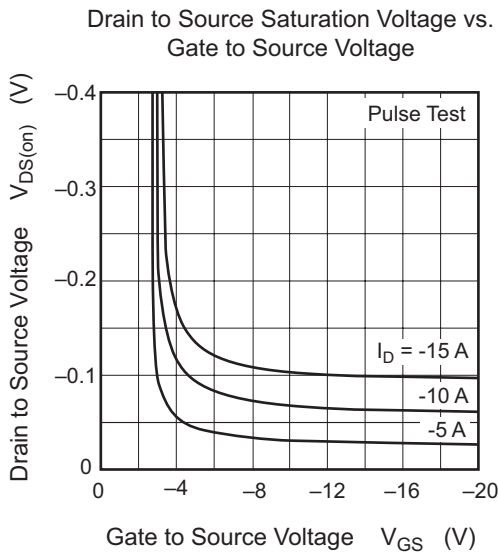
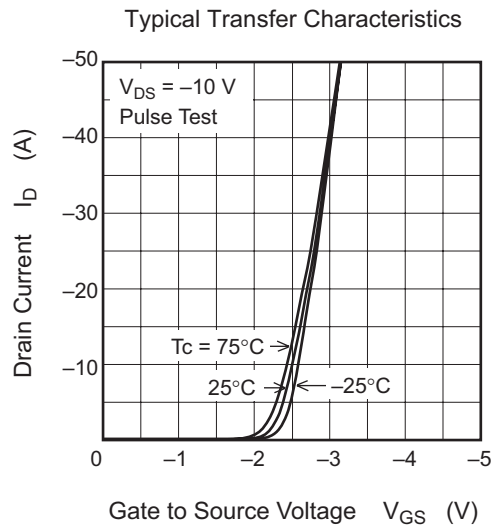
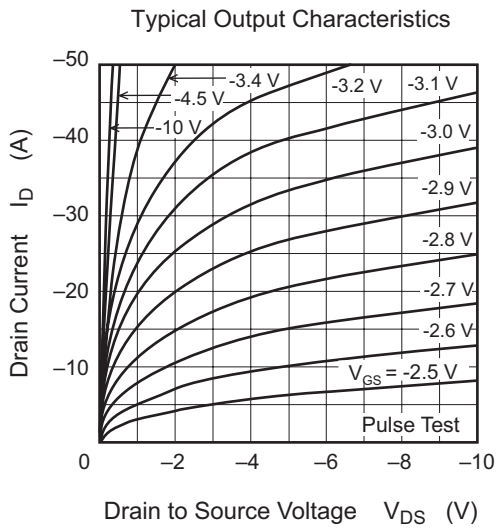
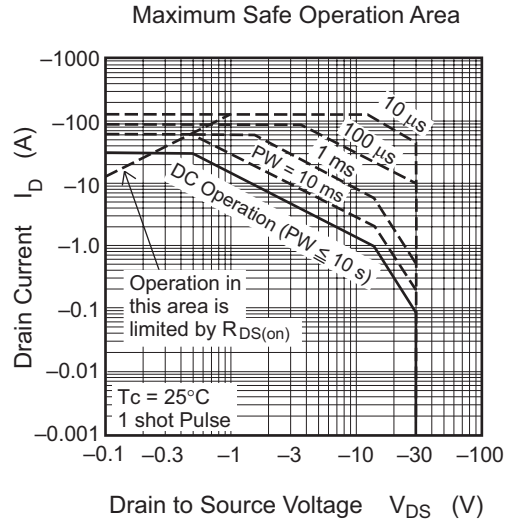
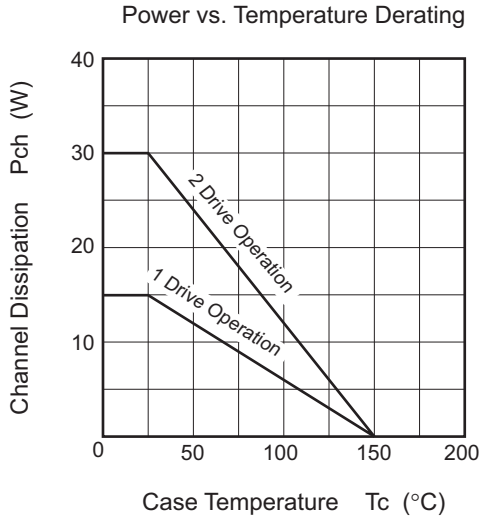
Electrical Characteristics

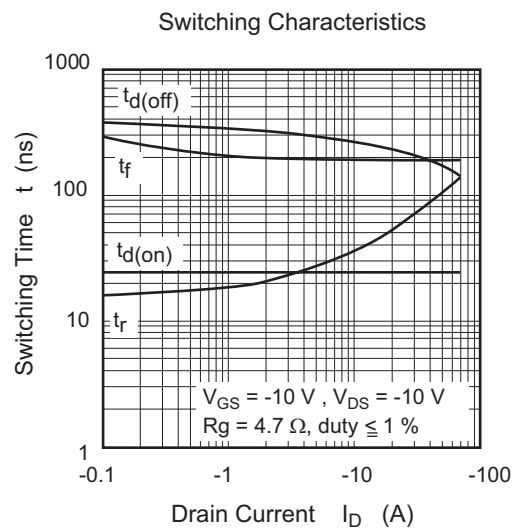
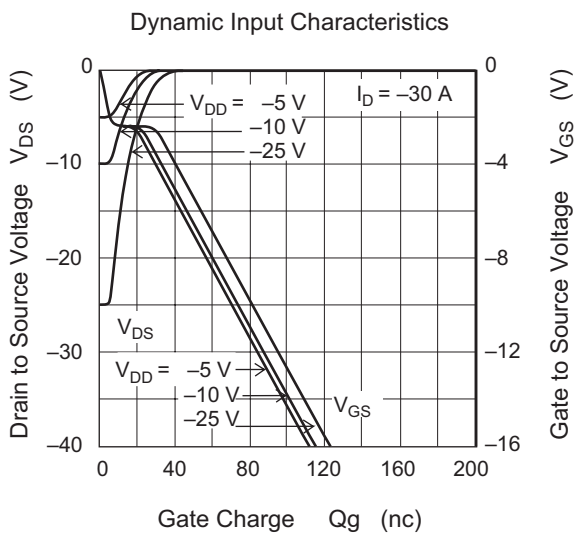
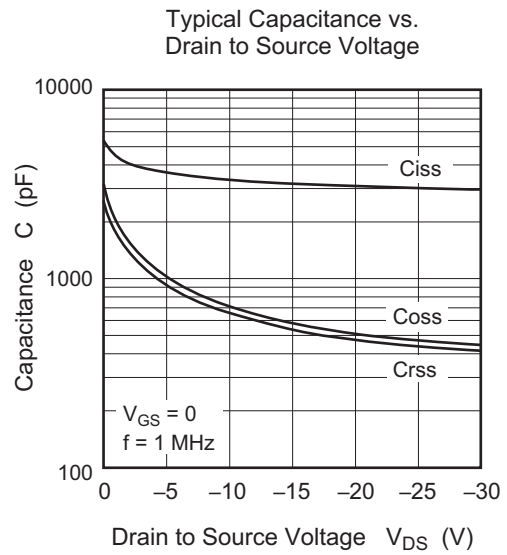
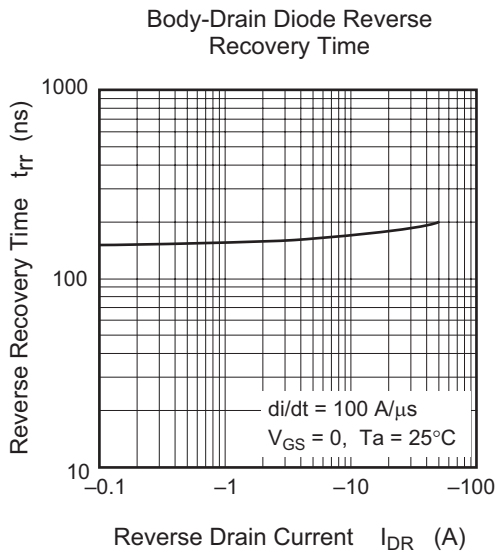
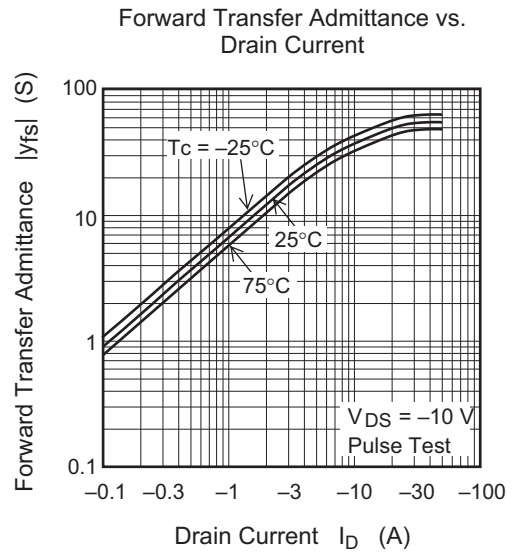
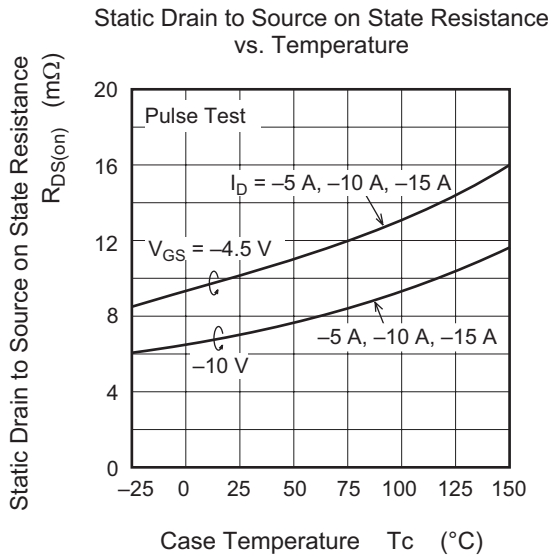
(Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	-30	—	—	V	$I_D = -10 \text{ mA}, V_{GS} = 0$
Gate to source leak current	I_{GSS}	—	—	± 0.1	μA	$V_{GS} = -20/+10 \text{ V}, V_{DS} = 0$
Zero gate voltage drain current	I_{DSS}	—	—	-1	μA	$V_{DS} = -30 \text{ V}, V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	-1.0	—	-2.5	V	$V_{DS} = -10 \text{ V}, I_D = -1 \text{ mA}$
Static drain to source on state resistance	$R_{DS(on)}$	—	7.0	9.0	$\text{m}\Omega$	$I_D = -15 \text{ A}, V_{GS} = -10 \text{ V}$ ^{Note4}
	$R_{DS(on)}$	—	10.0	14.5	$\text{m}\Omega$	$I_D = -15 \text{ A}, V_{GS} = -4.5 \text{ V}$ ^{Note4}
Forward transfer admittance	$ y_{fs} $	27	45	—	S	$I_D = -15 \text{ A}, V_{DS} = -10 \text{ V}$ ^{Note4}
Input capacitance	C_{iss}	—	3200	—	pF	$V_{DS} = -10 \text{ V}, V_{GS} = 0,$ $f = 1 \text{ MHz}$
Output capacitance	C_{oss}	—	720	—	pF	
Reverse transfer capacitance	C_{rss}	—	550	—	pF	
Total gate charge	Q_g	—	73	—	nc	$V_{DD} = -10 \text{ V}, V_{GS} = -10 \text{ V},$ $I_D = -30 \text{ A}$
Gate to source charge	Q_{gs}	—	8	—	nc	
Gate to drain charge	Q_{gd}	—	14	—	nc	
Turn-on delay time	$t_{d(on)}$	—	23	—	ns	$V_{GS} = -10 \text{ V}, I_D = -15 \text{ A},$ $V_{DD} \cong -10 \text{ V}, R_L = 0.67 \Omega,$ $R_g = 4.7 \Omega$
Rise time	t_r	—	48	—	ns	
Turn-off delay time	$t_{d(off)}$	—	247	—	ns	
Fall time	t_f	—	186	—	ns	
Body-drain diode forward voltage	V_{DF}	—	-0.91	-1.19	V	$I_F = -30 \text{ A}, V_{GS} = 0$ ^{Note4}
Body-drain diode reverse recovery time	t_{rr}	—	185	—	ns	$I_F = -30 \text{ A}, V_{GS} = 0$ $diF/dt = 100 \text{ A}/\mu\text{s}$

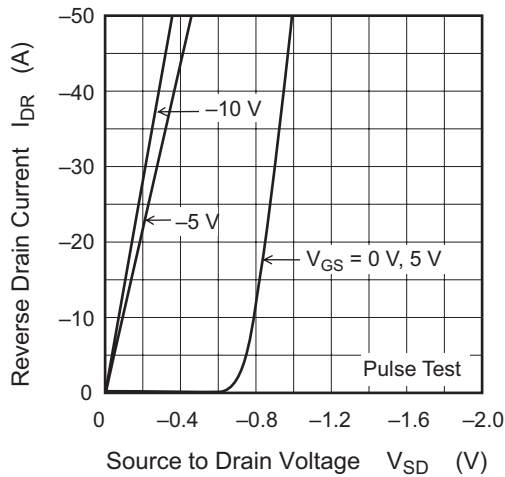
Notes: 4. Pulse test

Main Characteristics

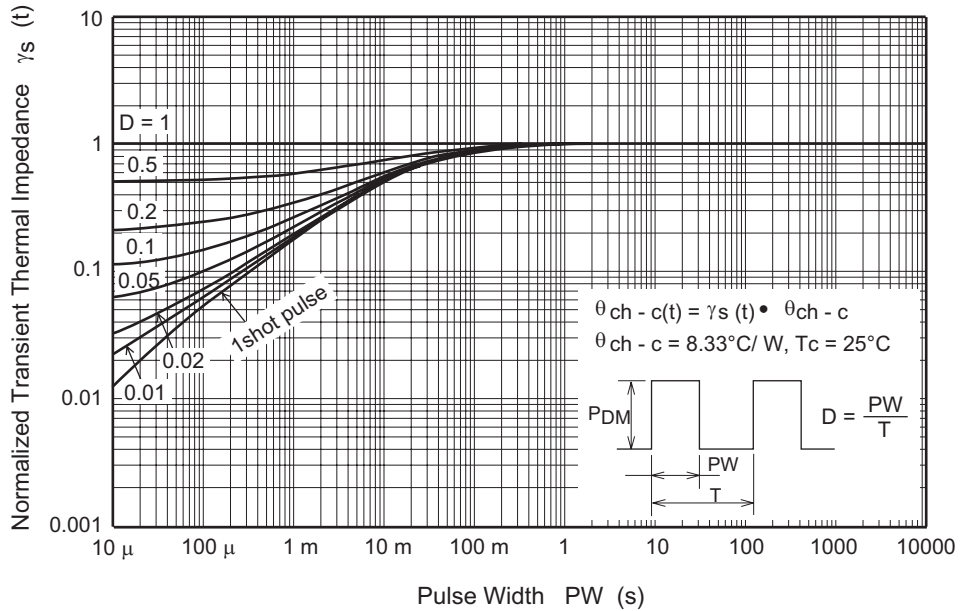




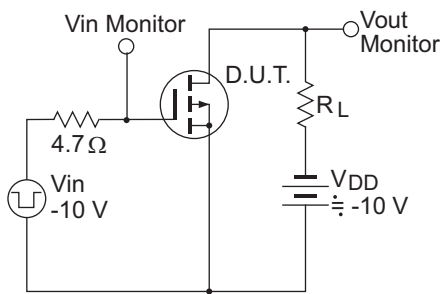
Reverse Drain Current vs. Source to Drain Voltage



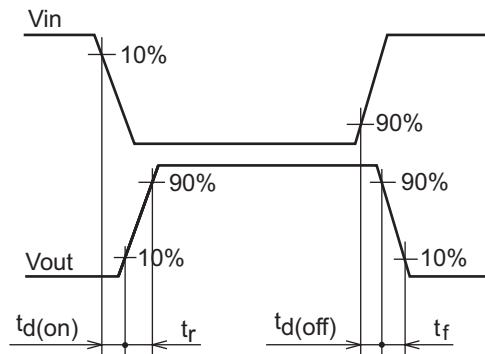
Normalized Transient Thermal Impedance vs. Pulse Width



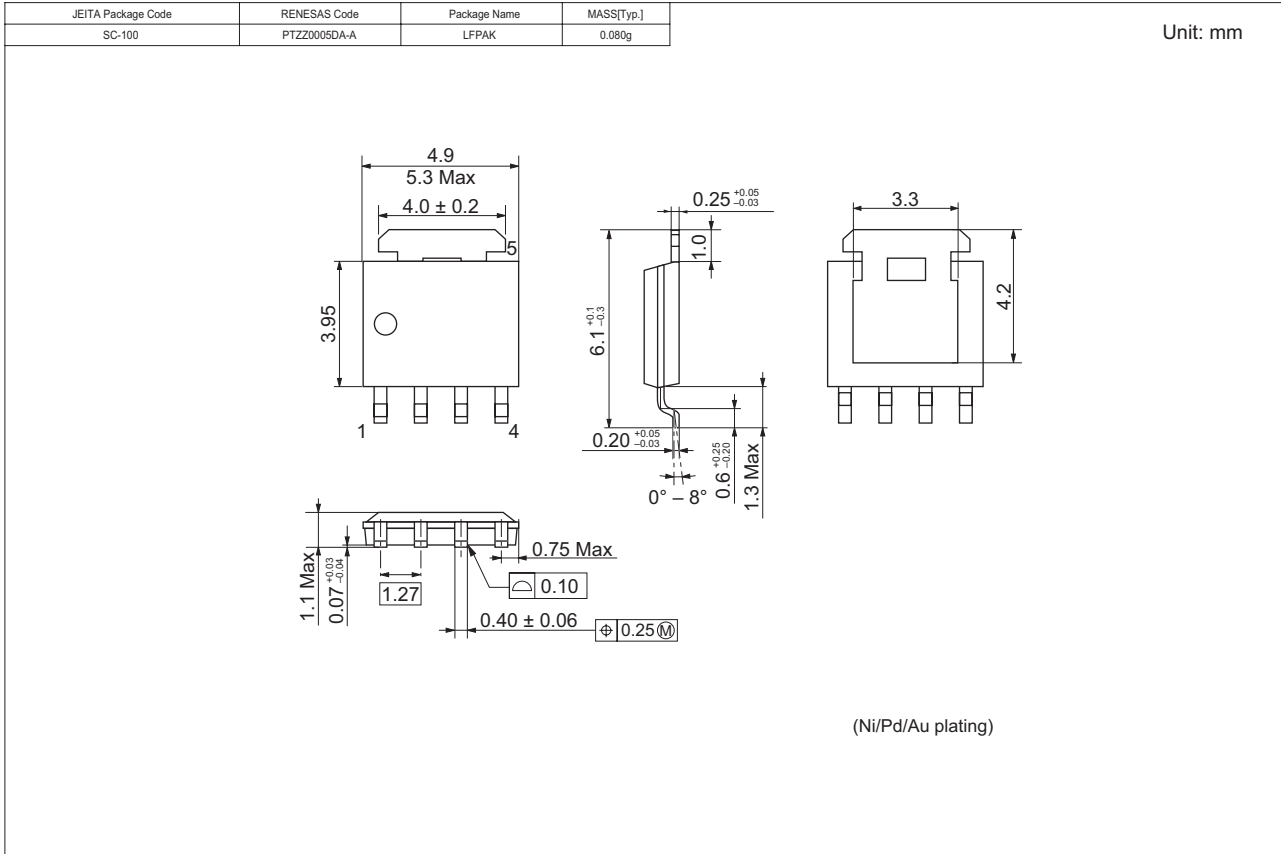
Switching Time Test Circuit



Waveform



Package Dimensions



Ordering Information

Part Name	Quantity	Shipping Container
HAT1139H-EL-E	2500 pcs	Taping

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